



Docket No. 740756-2119

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Hisashi OHTANI et al.

Serial No. 09/550,598

Filed: April 17, 2000

For: SEMICONDUCTOR DEVICE AND  
PROCESS FOR PRODUCING THE  
SAME

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TC 2500 MAIL ROOM

Group Art Unit: 2814

Examiner: P. Cao

Date: January 11, 2002

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CERTIFICATE OF MAILING

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*Eugene J. Cantrell*  
Eugene J. Cantrell

AMENDMENT

Honorable Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the non-final Office Action mailed October 11, 2001, please amend the  
above identified application as follows.

09/25/2002 5500598 00000001 192340 09550598  
01 FC:102 522.00 CH

IN THE CLAIMS:

Please cancel claims 13, 16, 17 and 19 without prejudice to or disclaimer of the subject  
matter disclosed therein.

Please amend claims 1-5, 14, 15, 18, and 20-26 as follows. Claims 1-5, 14, 15, 18, and  
20-26 are presented below in their amended form. The amendments to the above-noted claims  
are outlined in an Attachment to the Amendment using the conventional indication method of  
bracketing and underlining.

1. (Amended) A method for producing a semiconductor device comprising:
- forming a first conductive layer;
  - forming an insulating layer comprising an organic resin over said first conductive layer;
  - forming an opening in said insulating layer to expose said first conductive layer at a  
bottom of said opening;

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